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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

NOV 14 2002

PATENT & TRADEMARK OFFICE

re the Application of: **IRINO, Kiyoshi**

Serial No.: **09/428,052**

AF/2815
#20/6
Am dt
Group Art Unit: 2815 ~~2815~~

Filed: **October 27, 1999**

Examiner: **Jose R. Diaz**

P.T.O. Confirmation No.: **4139** *11/20/02*

For: **METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (As Amended)**

RESPONSE UNDER 37 CFR §1.116
- EXPEDITED RESPONSE -
GROUP ART UNIT 2815

BOX AF

Commissioner for Patents
Washington, D.C. 20231

November 14, 2002

Sir:

In response to the Office Action dated **August 14, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 10 as follows:

mult 4 → 10. (Six Times Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate by a thermal oxide film;

forming a gate electrode pattern on said gate oxide film such that said gate electrode pattern

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